

<b>Form PTO-1449 (Modified)</b>		<b>AMAT Atty Docket No.:</b> 005794 ALRT/ETCH/CONE <b>BSTZ Docket No.:</b> 4887P578		<b>Serial No.:</b> Not Yet Assigned	
List of Patents and Publications Statement (Use several sheets if necessary)			<b>Applicant:</b> Kawaguchi, et al.		
Page 1 of 3			<b>Filing Date:</b> Herewith		

J-857 U.S. PTO  
 09/978121  

 10/15/01

U.S. PATENT DOCUMENTS						
Examiner Initials	Document No.	Document No.	Inventor	Class	Sub-Class	Filing date if appropriate
<i>And</i>	AA	6,007,671	Fujimura, et al.	156	345	8/20/1996
	AB	5,403,436	Fujimura, et al.	156	643	7/11/1994
	AC	6,024,045	Kikuchi, et al.	118	723 ME	10/26/1998
	AD	5,773,201	Fujimura, et al.	430	329	2/9/1994
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	AF	5,174,856	Hwang, et al.	156	643	8/26/1991
	AG	5,200,031	Latchford, et al.	156	659.1	8/26/1991
	AH	5,221,424	Rhoades	156	643	11/21/1991
	AI	5,545,289	Chen, et al.	156	643.1	6/29/1994
	<i>And</i>	AJ	6,150,628	Smith, et al.	219	121.54
AK						

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No.	Document No.	Date	Country	Class	Sub-Class	Trans-lation	
<i>And</i>	AL	WO 01/11650 A1	2/15/2001	PCT	A1		
	AM						
	AN						
	AO						
	AP						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
<i>And</i>	AR	Kikuchi, et al., "Effects of H <sub>2</sub> O on Atomic Hydrogen Generation in Hydrogen Plasma," June 1993, Jpn. J. Appl Phys. Vol. 32 (1993) Part 1, No. 6B, pp. 3120-3124.
<i>And</i>	AS	Chang, et al., "Suppression of Copper Diffusion Through Barrier Metal-Free Hydrogen Silsesquioxane Dielectrics by NH <sub>3</sub> Plasma Treatment," June 2, 1999, Electrochemical and Solid State Letters, pp 634-636.
<i>And</i>	AT	Nakagawa, et al., "RIE-Lag-Less Etching by CH <sub>4</sub> /N <sub>2</sub> Plasma for Organic Low-k Dielectric," 2000, 2000 Dry Process Symposium, ULSI Process Technology Development Center, Semiconductor Company, Matsushita Electronics Corp., Institute for Semiconductor Technologies, ULVAC Japan Ltd., pp. 257-262.

Examiner <i>Allen Olson</i>	Date Considered <i>6.24.03</i>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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<b>List of Patents and Publications Statement</b>  (Use several sheets if necessary)		<b>Applicant:</b> Kawaguchi, et al.
Page 2 of 3		<b>Filing Date:</b> Herewith

  

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	AM						
	AN						
	AO						
	AP						

  

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
	AR	Morikawa, et al., "Organic Low-k Etching Process in Low Pressure and High Density NLD Plasma", 2000, 2000 Dry Process Symposium, pp. 263-268.
	AS	Janowiak, et al., "Etching of organic low dielectric constant material SiLK™ on the Lam Research Corporation 4520XLE™," J. Vac. Sci. Technol., Jul/Aug 2000, 2000 American Vacuum Society, pp. 1859-1863.
	AT	Chang, et al., "The Novel Improvement of Low Dielectric Constant Methylsilsesquioxane by N <sub>2</sub> O Plasma Treatment," Journal of The Electrochemical Society, October 20, 1998, pp. 3802-3806.
Examiner		Date Considered 6-24-03

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Page 3 of 3		<b>Filing Date:</b> Herewith

  

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	AM						
	AN						
	AO						
	AP						

  

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
<i>AL</i>	AR	Louis, et al., "Improved Post Etch Cleaning for low-k and copper integration for 0.18 $\mu$ m Technology," <i>Microelectronic Engineering</i> 46 (1999), pp. 307-310.
<i>AS</i>	AS	Kikuchi, et al., "Native Oxide Removal on Si Surfaces by NF <sub>3</sub> -Added Hydrogen and Water Vapor Plasma Downstream Treatment," <i>Jpn. J. Appl. Phys. Vol. 33</i> (1994), Part 1, No. 4B, April 1994, pp. 2207-2211.
<i>AT</i>	AT	Kikuchi, et al., "Cleaning of Silicon Surfaces by NF <sub>3</sub> - Added Hydrogen and Water-Vapor Plasma Downstream Treatment," <i>Jpn J. Appl. Phys. Vol. 35</i> (1996), Part 1, No. 2B, February 1996, pp. 1022-1026.
Examiner <i>Allen Olson</i>		Date Considered <i>6.24.03</i>

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Substitute for Form 1449/PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)

Complete if Known

Application Number	09/978,121
Filing Date	10/15/2001
First Named Inventor:	Kawaguchi
Art Unit	1733
Examiner Name	Unassigned
Attorney Docket Number	005794
	ALRT/ETCH/CONE/

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## U.S. PATENT DOCUMENTS

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (If known)				
AEO AEO		US-	6,235,453 B1	05-22-2001	You, et al.	
		US-	2001/0024769 A1	09-27-2001	Donoghue, et al.	
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## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
AEO			EP 0 463 870 A1		01-02-1992	Fujitsu Limited/Fujimura, et al.		

Examiner Signature	<i>[Signature]</i>	Date Considered	6-19-03
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Based on Form PTO/SB/08A (04-03) as modified by BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP on 05/09/03  
BSTZ Docket No.: 004887.P578

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